

Physics of Semiconductor Devices

2nd Edition



Contents

INTRODUCTION	1
PART I SEMICONDUCTOR PHYSICS	5
Chapter 1 Physics and Properties of Semiconductors— A Résumé	7
1.1 Introduction, 7	
1.2 Crystal Structure, 8	
1.3 Energy Bands, 12	
1.4 Carrier Concentration at Thermal Equilibrium, 16	
1.5 Carrier Transport Phenomena, 27	
1.6 Phonon Spectra and Optical, Thermal, and High-Field Properties of Semiconductors, 38	
1.7 Basic Equations for Semiconductor Device Operation, 50	
PART II BIPOLAR DEVICES	61
Chapter 2 p-n Junction Diode	63
2.1 Introduction, 63	
2.2 Basic Device Technology, 64	
2.3 Depletion Region and Depletion Capacitance, 74	
2.4 Current-Voltage Characteristics, 84	
2.5 Junction Breakdown, 96	
2.6 Transient Behavior and Noise, 108	
2.7 Terminal Functions, 112	
2.8 Heterojunction, 122	

Chapter 3 Bipolar Transistor

133

- 3.1 Introduction, 133
- 3.2 Static Characteristics, 134
- 3.3 Microwave Transistor, 156
- 3.4 Power Transistor, 169
- 3.5 Switching Transistor, 175
- 3.6 Related Device Structures, 181

Chapter 4 Thyristors

190

- 4.1 Introduction, 190
- 4.2 Basic Characteristics, 191
- 4.3 Shockley Diode and Three-Terminal Thyristor, 209
- 4.4 Related Power Thyristors, 222
- 4.5 Diac and Triac, 229
- 4.6 Unijunction Transistor and Trigger Thyristors, 234
- 4.7 Field-Controlled Thyristor, 238

PART III UNIPOLAR DEVICES

243

Chapter 5 Metal-Semiconductor Contacts

245

- 5.1 Introduction, 245
- 5.2 Energy-Band Relation, 246
- 5.3 Schottky Effect, 250
- 5.4 Current Transport Processes, 254
- 5.5 Characterization of Barrier Height, 270
- 5.6 Device Structures, 297
- 5.7 Ohmic Contact, 304

Chapter 6 JFET and MESFET

312

- 6.1 Introduction, 312
- 6.2 Basic Device Characteristics, 314
- 6.3 General Characteristics, 324
- 6.4 Microwave Performance, 341
- 6.5 Related Field-Effect Devices, 351

Chapter 7 MIS Diode and CCD

362

- 7.1 Introduction, 362
- 7.2 Ideal MIS Diode, 363
- 7.3 Si-SiO₂ MOS Diode, 379
- 7.4 Charge-Coupled Device, 407

Chapter 8 MOSFET	xi
8.1 Introduction, 431	431
8.2 Basic Device Characteristics, 433	
8.3 Nonuniform Doping and Buried-Channel Devices, 456	
8.4 Short-Channel Effects, 469	
8.5 MOSFET Structures, 486	
8.6 Nonvolatile Memory Devices, 496	
PART IV SPECIAL MICROWAVE DEVICES	511
Chapter 9 Tunnel Devices	513
9.1 Introduction, 513	
9.2 Tunnel Diode, 516	
9.3 Backward Diode, 537	
9.4 MIS Tunnel Diode, 540	
9.5 MIS Switch Diode, 549	
9.6 MIM Tunnel Diode, 553	
9.7 Tunnel Transistor, 558	
Chapter 10 IMPATT and Related Transit-Time Diodes	566
10.1 Introduction, 566	
10.2 Static Characteristics, 568	
10.3 Dynamic Characteristics, 577	
10.4 Power and Efficiency, 585	
10.5 Noise Behavior, 599	
10.6 Device Design and Performance, 604	
10.7 BARITT and DOVETT Diodes, 613	
10.8 TRAPATT Diode, 627	
Chapter 11 Transferred-Electron Devices	637
11.1 Introduction, 637	
11.2 Transferred-Electron Effect, 638	
11.3 Modes of Operation, 651	
11.4 Device Performances, 667	
PART V PHOTONIC DEVICES	679
Chapter 12 LED and Semiconductor Lasers	681
12.1 Introduction, 681	
12.2 Radiative Transitions, 682	

- 12.3 Light-Emitting Diodes, 689
- 12.4 Semiconductor Laser Physics, 704
- 12.5 Laser Operating Characteristics, 724

Chapter 13 Photodetectors 743

- 13.1 Introduction, 743
- 13.2 Photoconductor, 744
- 13.3 Photodiode, 749
- 13.4 Avalanche Photodiode, 766
- 13.5 Phototransistor, 782

Chapter 14 Solar Cells 790

- 14.1 Introduction, 790
- 14.2 Solar Radiation and Ideal Conversion Efficiency, 791
- 14.3 *p-n* Junction Solar Cells, 799
- 14.4 Heterojunction, Interface, and Thin-Film Solar Cells, 816
- 14.5 Optical Concentration, 830

APPENDIXES 839

- A. List of Symbols, 841
- B. International System of Units, 844
- C. Unit Prefixes, 845
- D. Greek Alphabet, 846
- E. Physical Constants, 847
- F. Lattice Constants, 848
- G. Properties of Important Semiconductors, 849
- H. Properties of Ge, Si, and GaAs at 300 K, 850
- I. Properties of SiO₂ and Si₃N₄ at 300 K, 851

INDEX 853